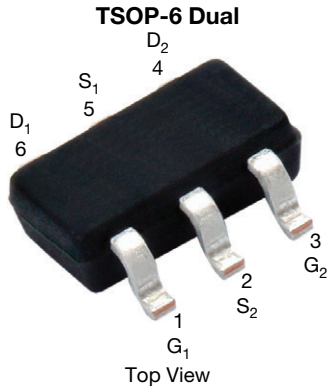


Automotive Dual P-Channel 30 V (D-S) 175 °C MOSFET



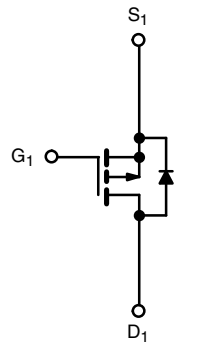
Marking Code: 9B

PRODUCT SUMMARY	
V_{DS} (V)	-30
$R_{DS(on)}$ (Ω) at $V_{GS} = -10$ V	-0.155
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5$ V	-0.300
I_D (A)	-2.32
Configuration	Dual
Package	TSOP-6

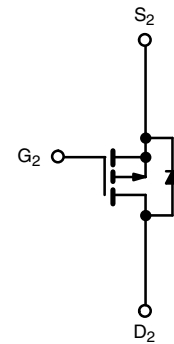
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE


RoHS
 COMPLIANT
 HALOGEN
FREE


P-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V_{DS}	-30	V	
Gate-source voltage	V_{GS}	± 20		
Continuous drain current ($T_J = 150$ °C) ^a	$T_C = 25$ °C	I_D	-2.5	A
	$T_C = 125$ °C		-1.5	
Pulsed drain current	I_{DM}	-10.2	A	
Continuous source current (diode conduction) ^a	I_S	-2.1		
Maximum power dissipation ^a	$T_C = 25$ °C	P_D	1.67	W
	$T_C = 125$ °C		0.56	
Unclamped inductive surge UIS	I_{AV}	7	A	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Maximum junction-to-ambient ^a	Steady state	R_{thJA}	150	°C/W
Maximum junction-to-foot (drain)	Steady state	R_{thJF}	90	

Note

a. Surface mounted on 1" x 1" FR4 board



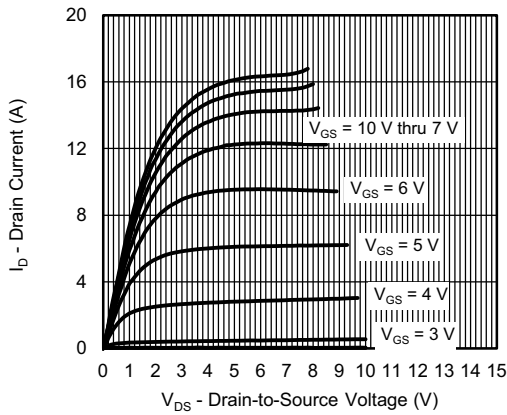
SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$		-0.6	-	-1.5	V
Gate-body leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{GS} = 0 \text{ V}$	$V_{DS} = -30 \text{ V}$	-	-	-1	μA
		$V_{GS} = 0 \text{ V}$	$V_{DS} = -30 \text{ V}, T_J = 55^\circ\text{C}$	-	-	-5	
On-state drain current ^a	$I_{D(on)}$	$V_{GS} = -10 \text{ V}$	$V_{DS} \leq -5 \text{ V}$	-4	-	-	A
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = -10 \text{ V}$	$I_D = -0.4 \text{ A}$	-	0.140	0.155	Ω
		$V_{GS} = -4.5 \text{ V}$	$I_D = -0.2 \text{ A}$	-	0.265	0.300	
Forward transconductance ^a	g_{fs}	$V_{DS} = -5 \text{ V}, I_D = -1 \text{ A}$		-	2.2	-	S
Diode forward voltage ^a	V_{SD}	$I_S = -0.5 \text{ A}, V_{GS} = 0 \text{ V}$		-	-0.83	-1.1	V
Dynamic ^b							
Total gate charge	Q_g	$V_{GS} = -10 \text{ V}$	$V_{DS} = -15 \text{ V}, I_D = -3 \text{ A}$	-	8.6	11.1	nC
Gate-source charge	Q_{gs}			-	1.2	-	
Gate-drain charge	Q_{gd}			-	3	-	
Gate resistance	R_g	$f = 1 \text{ MHz}$		2.5	-	7.2	Ω
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -10 \text{ V}, R_L = 10 \Omega$ $I_D \cong -1 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \text{ k}\Omega$		-	5.7	8	ns
Rise time	t_r			-	3	4	
Turn-off delay time	$t_{d(off)}$			-	13.8	18	
Fall time	t_f			-	2	3	

Notes

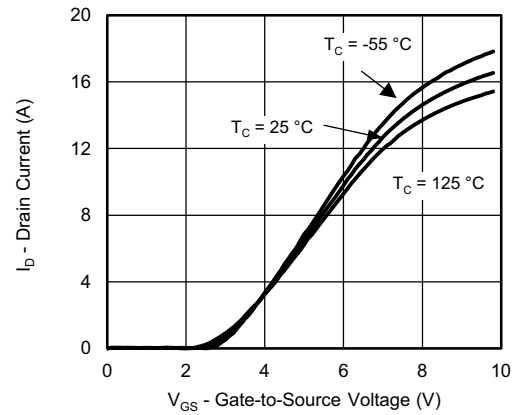
- a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

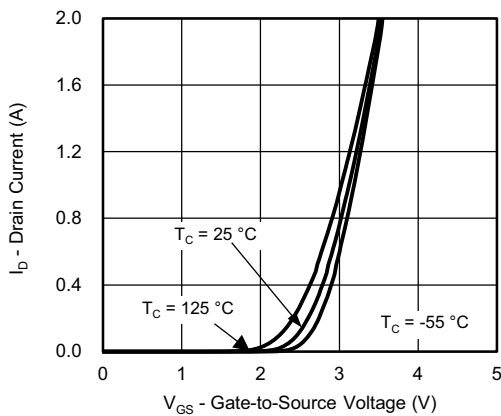
TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



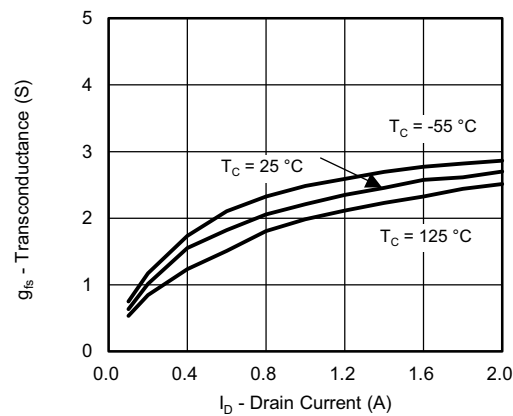
Output Characteristics



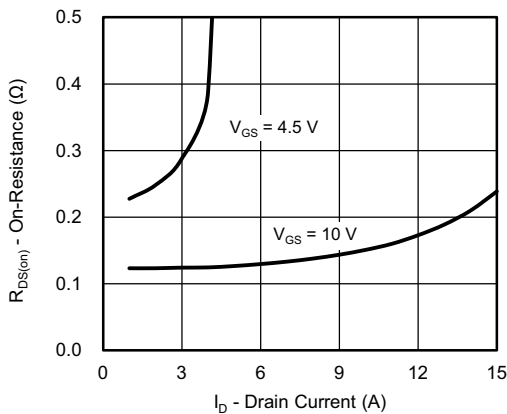
Transfer Characteristics



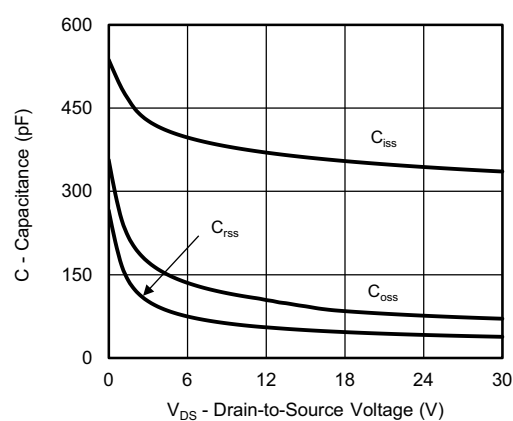
Transfer Characteristics



Transconductance

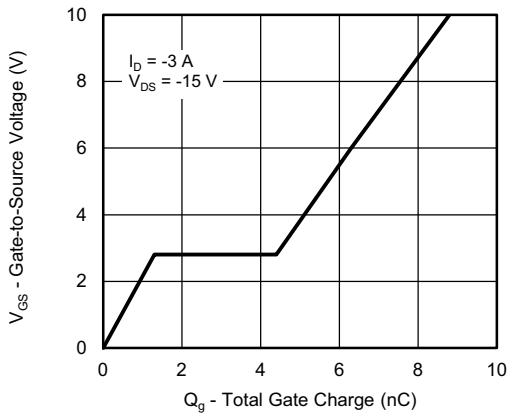


On-Resistance vs. Drain Current

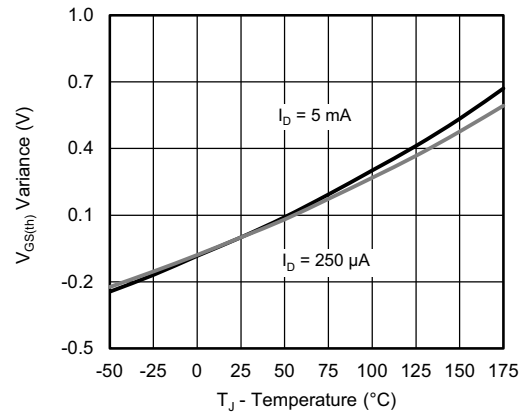


Capacitance

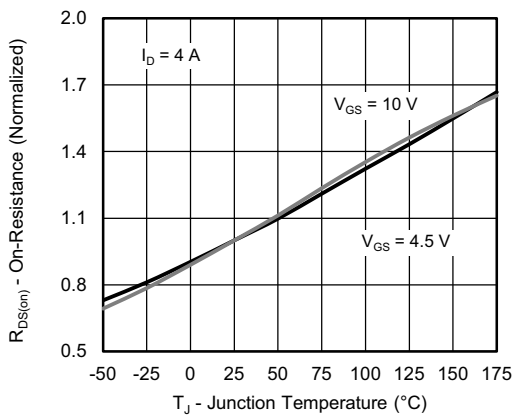
TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



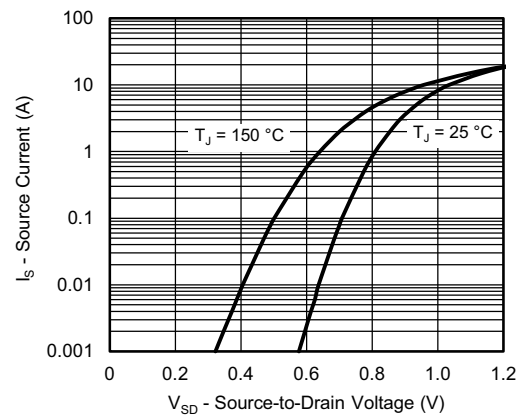
Gate Charge



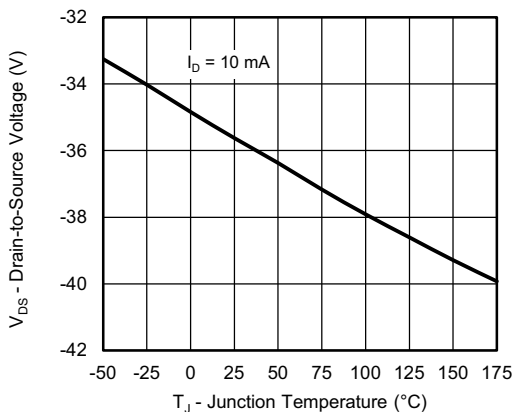
Threshold Voltage



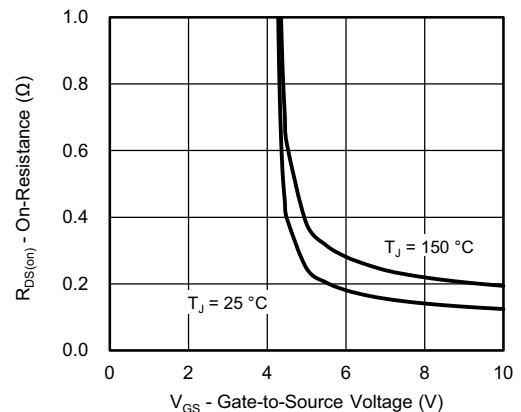
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



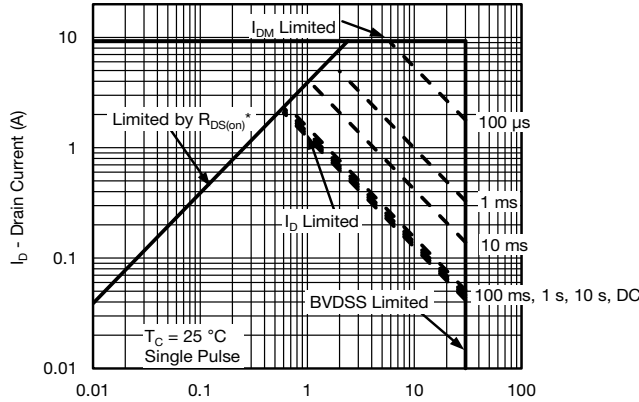
Drain Source Breakdown vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

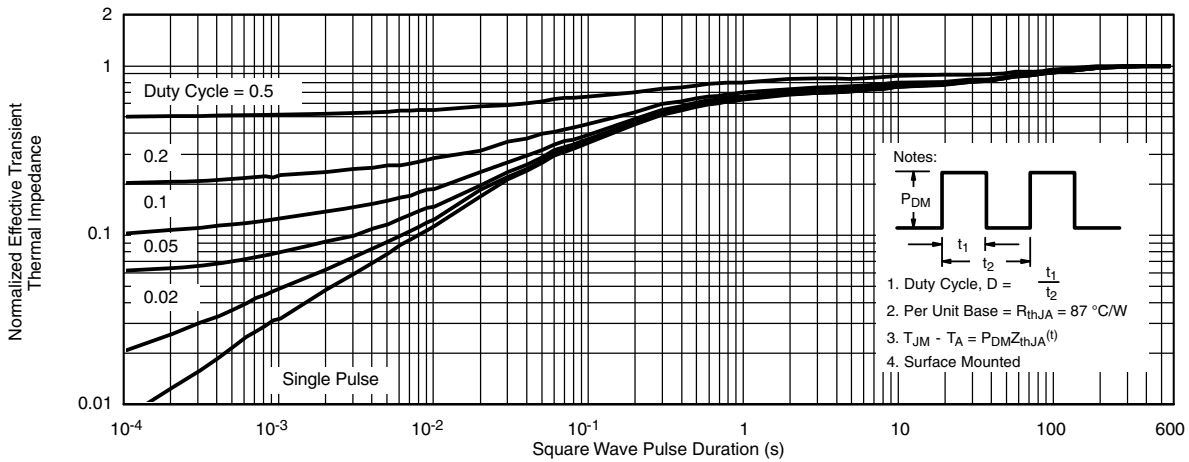


TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)

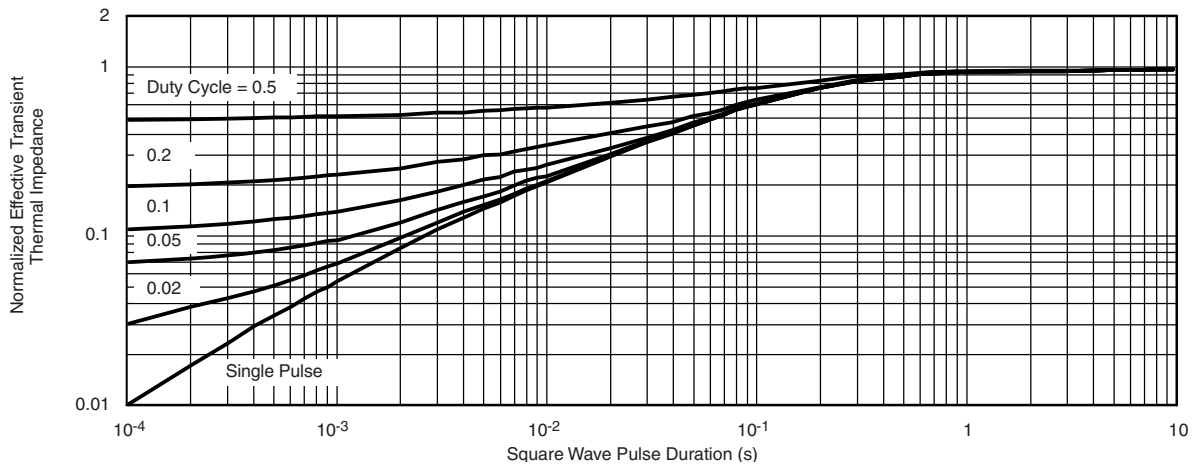


V_{DS} - Drain-to-Source Voltage (V)
 * $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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